



# 2N7002

## 60V N-Channel Enhancement Mode MOSFET

### FEATURES

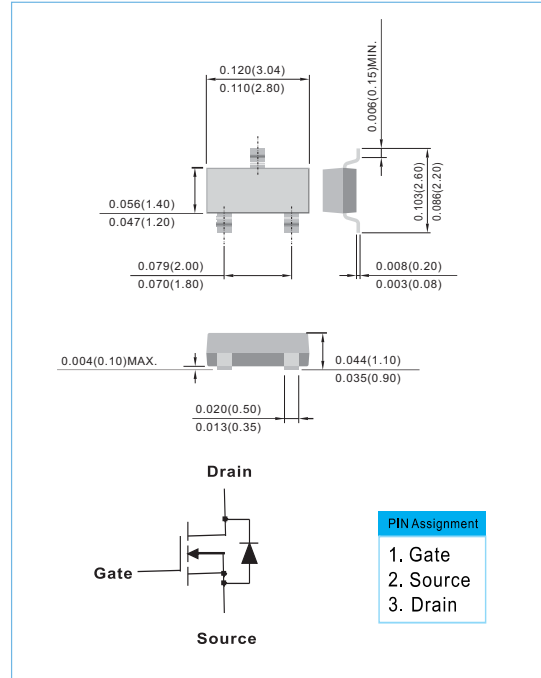
- $R_{DS(ON)}, V_{GS}@10V, I_{DS}@500mA=5\Omega$
- $R_{DS(ON)}, V_{GS}@4.5V, I_{DS}@75mA=7.5\Omega$
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### MECHANICAL DATA

- Case: SOT-23 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Apporx. Weight : 0.0003 ounces, 0.0084grams
- Marking : S72

SOT-23

Unit: inch ( mm )



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	250	mA
Pulsed Drain Current <sup>1)</sup>	$I_{DM}$	1300	mA
Maximum Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$ 350 $T_A=75^\circ\text{C}$ 210	mW
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to + 150	$^\circ\text{C}$
Junction-to Ambient Thermal Resistance(PCB mounted) <sup>2)</sup>	$R_{\theta JA}$	357	$^\circ\text{C/W}$

- Note: 1. Maximum DC current limited by the package  
2. Surface mounted on FR4 board,  $t < 10$  sec

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